

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a first fin type pattern on a substrate, a second fin type pattern, parallel to the first fin type pattern, on the substrate, and an epitaxial pattern on the first and second fin type patterns. The epitaxial pattern may include a shared semiconductor pattern on the first fin type pattern and the second fin type pattern. The shared semiconductor pattern may include a first sidewall adjacent to the first fin type pattern and a second sidewall adjacent to the second fin type pattern. The first sidewall may include a first lower facet, a first upper facet on the first lower facet and a first connecting curved surface connecting the first lower and upper facets. The second sidewall may include a second lower facet, a second upper facet on the second lower facet and a second connecting curved surface connecting the second lower and upper facets.

FIG. 4